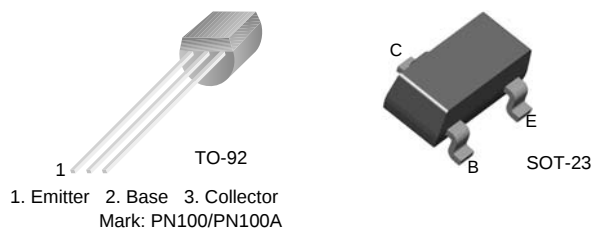


PN100/PN100A/MMBT100/MMBT100A

NPN General Purpose Amplifier

- This device is designed for general purpose amplifier applications at collector currents to 300mA.
- Sourced from process 10.



Absolute Maximum Ratings* $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{CEO}	Collector-Emitter Voltage		45
V_{CBO}	Collector-Base Voltage		75
V_{EBO}	Emitter-Base Voltage		6.0
I_C	Collector current	- Continuous	500
T_J, T_{stg}	Junction and Storage Temperature		$-55 \sim +150$

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1. These ratings are based on a maximum junction temperature of 150 degrees C.
2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

* Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

Thermal Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Max.		Units
		PN100 PN100A	*MMBT100 *MMBT100A	
P_D	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	mW mW/ $^\circ\text{C}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	$^\circ\text{C/W}$

* Device mounted on FR-4 PCB $1.6'' \times 1.6'' \times 0.06''$

Electrical Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Characteristics					
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = 10\mu\text{A}, I_E = 0$	75		V
BV_{CEO}	Collector-Emitter Breakdown Voltage *	$I_C = 1\text{mA}, I_B = 0$	45		V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 10\mu\text{A}, I_C = 0$	6.0		V
I_{CBO}	Collector-Base Cutoff Current	$V_{CB} = 60\text{V}$		50	nA
I_{CES}	Collector-Emitter Cutoff Current	$V_{CE} = 40\text{V}$		50	nA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 4\text{V}$		50	nA
On Characteristics					
h_{FE}	DC Current Gain	$I_C = 100\mu\text{A}, V_{CE} = 1.0\text{V}$ $I_C = 10\text{mA}, V_{CE} = 1.0\text{V}$ $I_C = 100\text{mA}, V_{CE} = 1.0\text{V}^*$ $I_C = 150\text{mA}, V_{CE} = 5.0\text{V}^*$	100 100A 100 100A 100 100A	80 240 100 300 100 100 350 100	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 200\text{mA}, I_B = 20\text{mA}$		0.2 0.4	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 200\text{mA}, I_B = 20\text{mA}$		0.85 1.0	V V
Small Signal Characteristics					
f_T	Current Gain Bandwidth Product	$V_{CE} = 20\text{V}, I_C = 20\text{mA}$		250	MHz
C_{obo}	Output Capacitance	$V_{CB} = 5.0\text{V}, f = 1.0\text{MHz}$		4.5	pF
NF	Noise Figure	$I_C = 100\mu\text{A}, V_{CE} = 5.0\text{V}$ $R_G = 2.0\text{k}\Omega, f = 1.0\text{KHz}$	100 100A	5.0 4.0	dB dB

* Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2.0\%$

Typical Characteristics

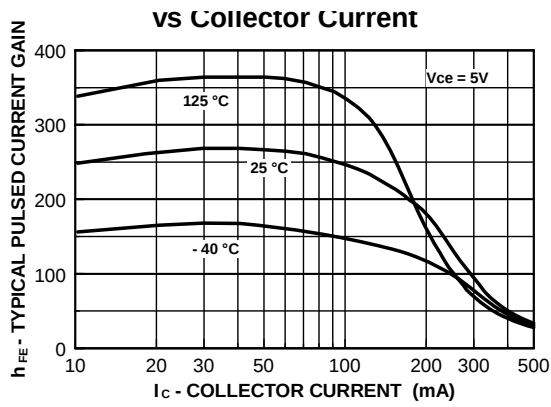


Figure 1. Typical Pulsed Current Gain vs Collector Current

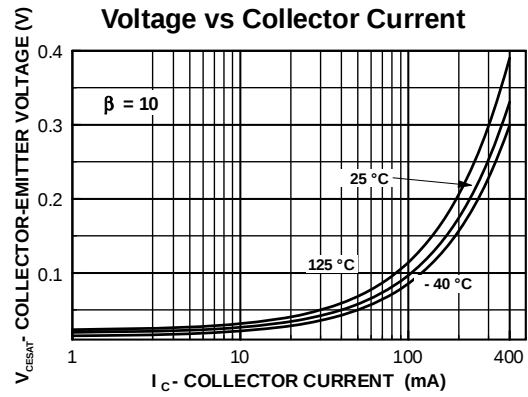


Figure 2. Collector-Emitter Saturation Voltage vs Collector Current

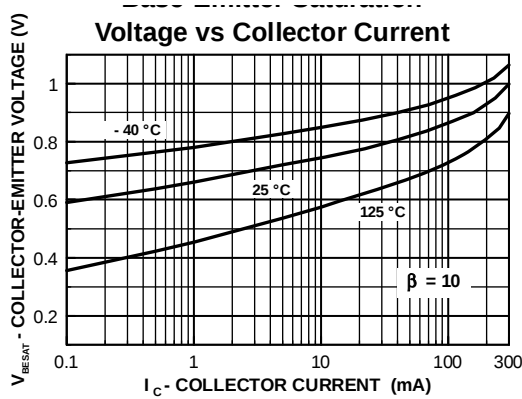


Figure 3. Base-Emitter Saturation Voltage vs Collector Current

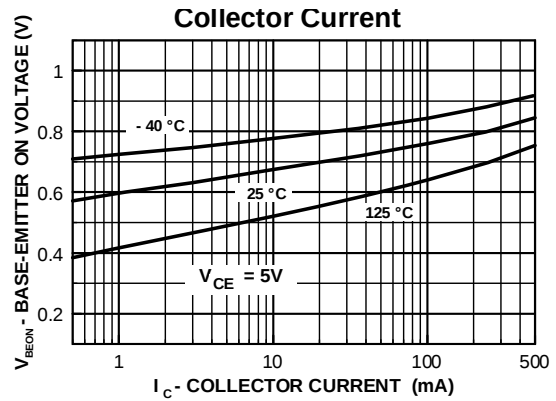


Figure 4. Base-Emitter On Voltage vs Collector Current

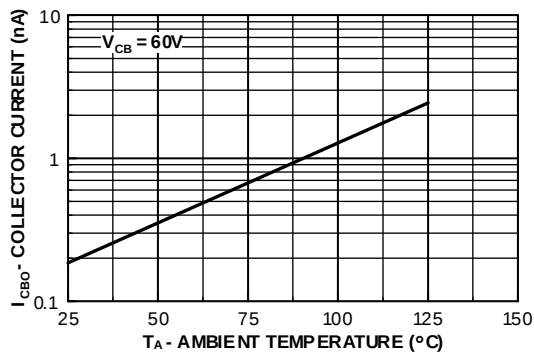


Figure 5. Collector Cutoff Current vs Ambient Temperature

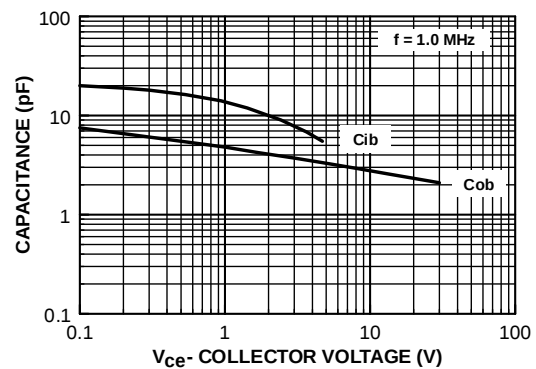


Figure 6. Input and Output Capacitance vs Reverse Voltage

Typical Characteristics (Continued)

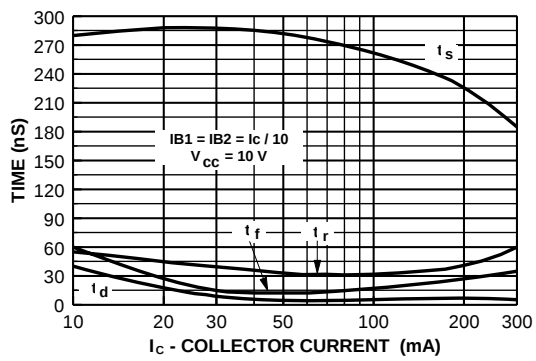


Figure 7. Switching Times vs Collector Current

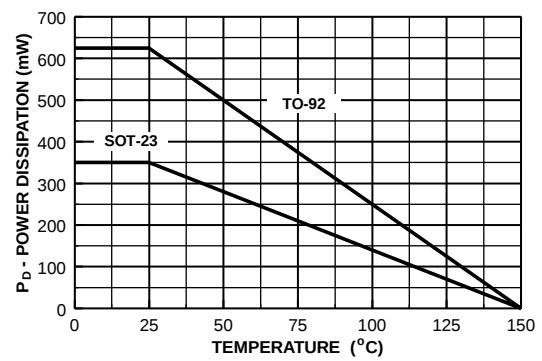
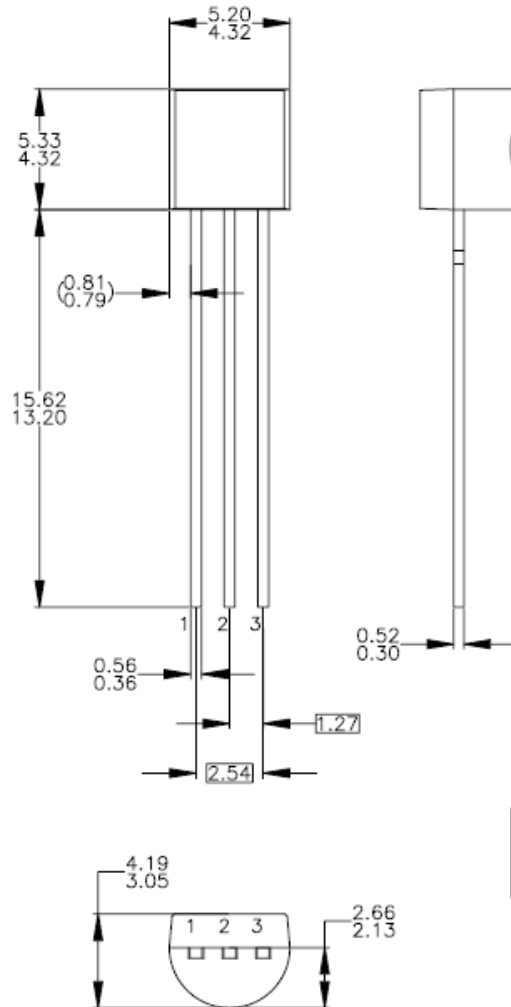


Figure 8. Power Dissipation vs Ambient Temperature

Package Dimension (TO92)



NOTES: UNLESS OTHERWISE SPECIFIED

- A) DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DRAWING CONFORMS TO ASME Y14.5M-1994.
- D) TO-92 (92,94,96,97,98) PIN CONFIGURATION:

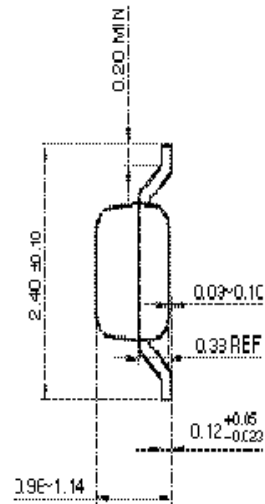
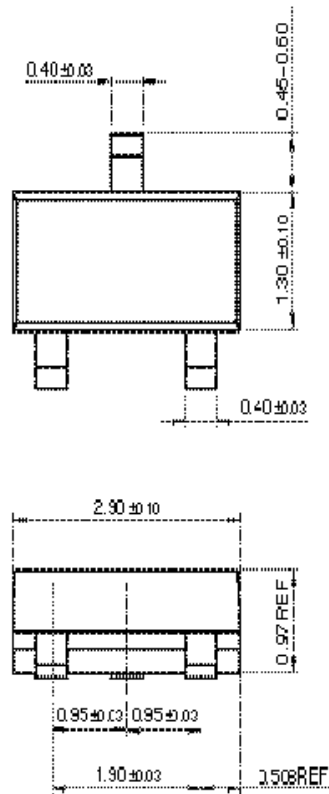
PIN	92	94	96	97	98
1	E S S	E S S	B D G	C G D	C G D
2	B D G	C G D	E S S	B D G	E S S
3	C G D	B D G	C G D	E S S	B D G

LEGEND:

P - BIPOLAR E - EMITTER D - DRAIN
F - JFET B - BASE S - SOURCE
M - DMOS C - COLLECTOR G - GATE

- E) FOR PACKAGE 92, 94, 96, 97 AND 98:
PIN CONFIGURATION DRAIN "D" AND SOURCE "S"
ARE INTERCHANGEABLE AT JFET "F" OPTION.
- F) DRAWING FILENAME: MKT-ZA030REV3.

Package Dimension (SOT23)



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CTL [™]	IntelliMAX [™]	Programmable Active Droop [™]	TinyBoost [™]
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EcoSPARK [®]	MegaBuck [™]	QS [™]	TinyLogic [®]
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FAST [®]	OPTOLOGIC [®]	STEALTH [™]	UHC [®]
FastvCore [™]	OPTOPLANAR [®]	SuperFET [™]	UniFET [™]
FPS [™]		SuperSOT [™] -3	VCX [™]
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